

P-Channel Power MOSFET

FEATURES

- Advance trench process technology
- RoHS compliant
- Halogen-free

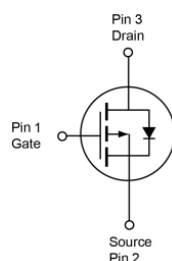
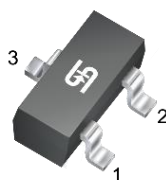
APPLICATIONS

- Power management
- Load switch
- Battery protection

KEY PERFORMANCE PARAMETERS		
PARAMETER	VALUE	UNIT
V_{DS}	-20	V
$R_{DS(on)}$ (max)	$V_{GS} = -4.5V$	39
	$V_{GS} = -2.5V$	52
	$V_{GS} = -1.8V$	68
Q_g	9.5	nC



SOT-23



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Continuous Drain Current	I_D	-4.3	A
Pulsed Drain Current (Note 1)	I_{DM}	-17.2	A
Total Power Dissipation	P_D	1.04	W
		0.67	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Ambient Thermal Resistance (Note 2)	$R_{\theta JA}$	120	$^\circ\text{C/W}$

Notes:

1. Pulse Width $\leq 100\mu\text{s}$.
2. Device on a PCB FR4 with 1 in² (single layer, 2 oz thickness) copper area for drain connection.

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = -250μA	BV _{DSS}	-20	--	--	V
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	V _{GS(TH)}	-0.4	-0.6	-1	V
Gate Body Leakage	V _{GS} = ±8V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} = 0V	I _{DSS}	--	--	-1	μA
Drain-Source On-State Resistance	V _{GS} = -4.5V, I _D = -4.3A	R _{DS(on)}	--	28	39	mΩ
	V _{GS} = -2.5V, I _D = -3.7A		--	36	52	
	V _{GS} = -1.8V, I _D = -2.9A		--	46	68	
Forward Transconductance	V _{DS} = -10V, I _D = -1.1A	g _{fs}	--	9.2	--	S
Dynamic (Note 4)						
Total Gate Charge	V _{DS} = -10V, I _D = -4.3A, V _{GS} = -4.5V	Q _g	--	9.5	--	nC
Gate-Source Charge		Q _{gs}	--	0.9	--	
Gate-Drain Charge		Q _{gd}	--	2.6	--	
Input Capacitance	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz	C _{iss}	--	769	--	pF
Output Capacitance		C _{oss}	--	112	--	
Reverse Transfer Capacitance		C _{rss}	--	106	--	
Switching (Note 5)						
Turn-On Delay Time	V _{DD} = -10V, R _G = 6Ω, I _D = -4.3A, V _{GS} = -4.5V	t _{d(on)}	--	4.6	--	ns
Turn-On Rise Time		t _r	--	36	--	
Turn-Off Delay Time		t _{d(off)}	--	83	--	
Turn-Off Fall Time		t _f	--	56	--	
Source-Drain Diode						
Forward Voltage (Note 3)	I _S = -4.3A, V _{GS} = 0V	V _{SD}	--	-0.7	-1.2	V

Notes:

- Pulse test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- Defined by design. Not subject to production test.
- Switching time is essentially independent of operating temperature.

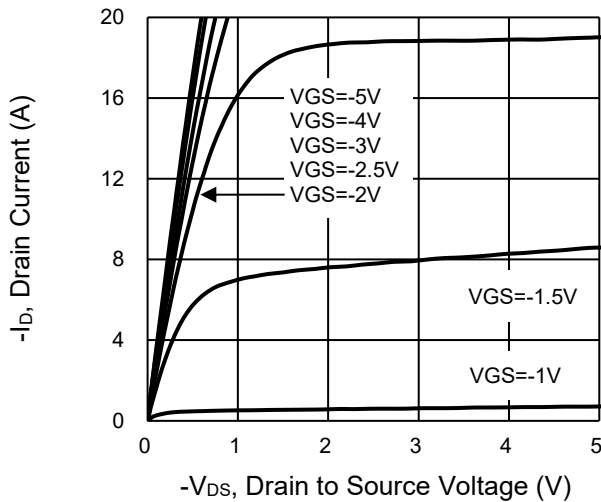
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM2323CX RFG	SOT-23	3kpcs / 7" Reel

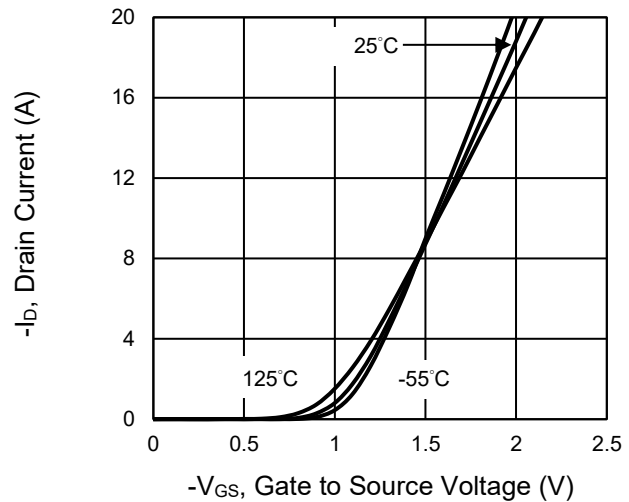
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

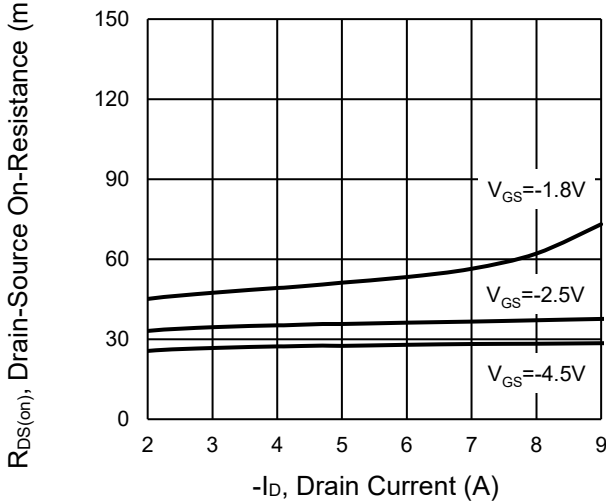
Output Characteristics



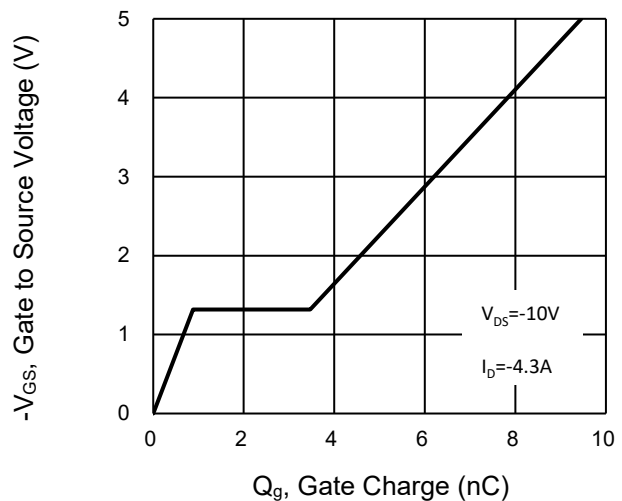
Transfer Characteristics



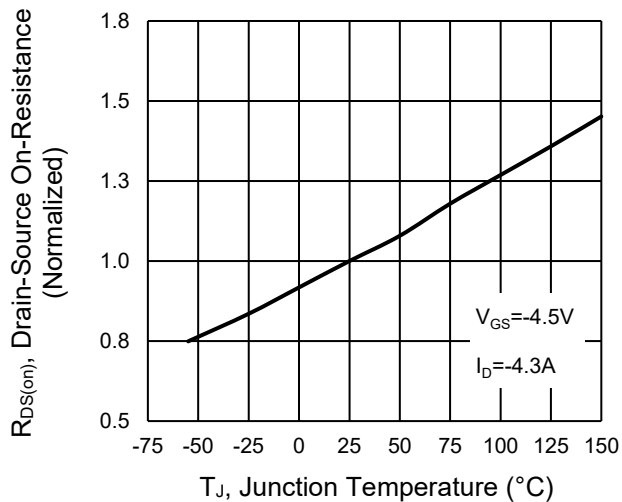
On-Resistance vs. Drain Current



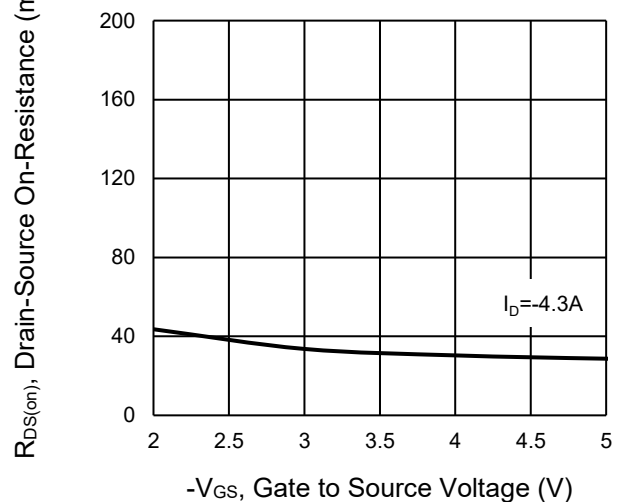
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



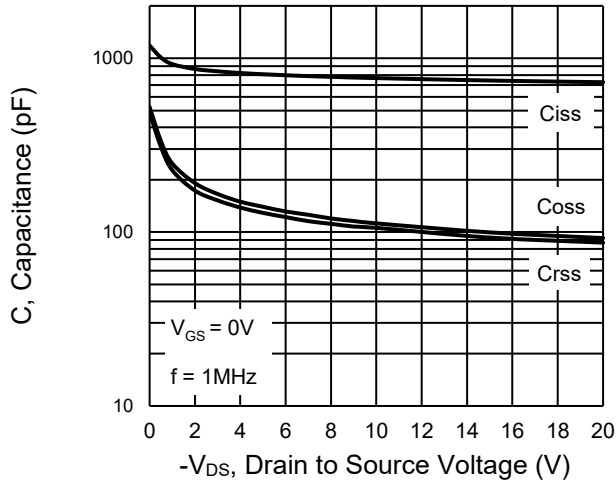
On-Resistance vs. Gate-Source Voltage



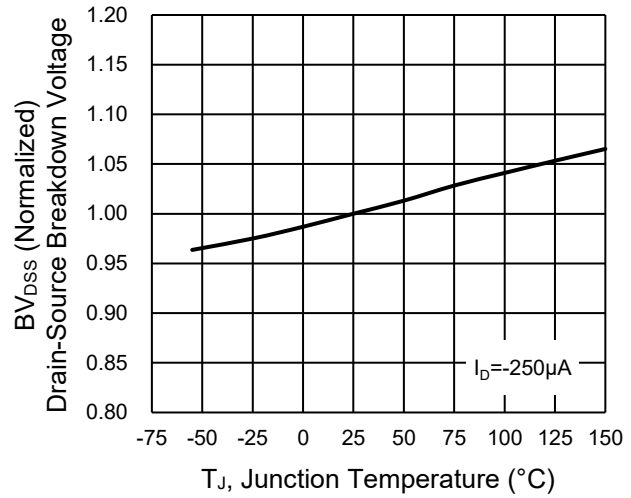
CHARACTERISTICS CURVES

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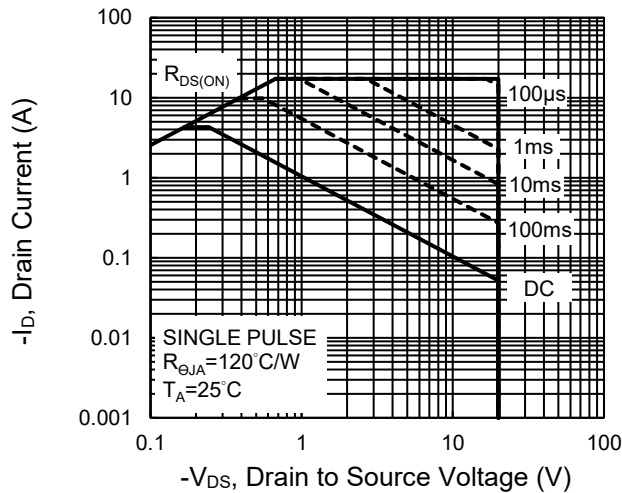
Capacitance vs. Drain-Source Voltage



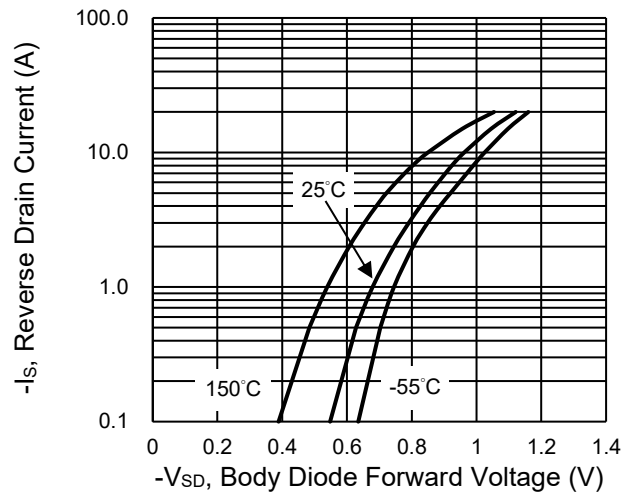
BV_{DSS} vs. Junction Temperature



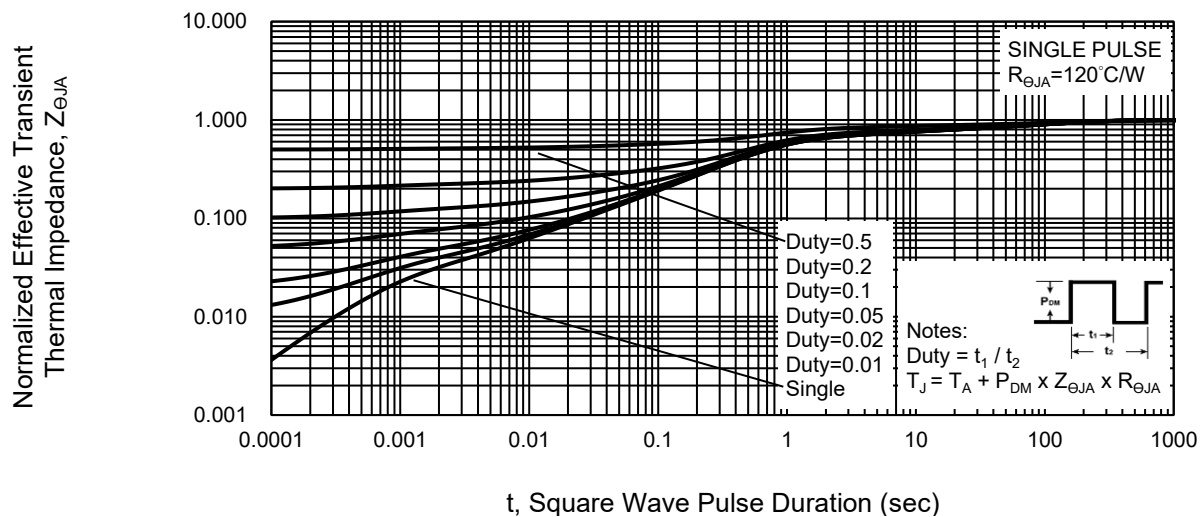
Maximum Safe Operating Area, Junction-to-Ambient



Source-Drain Diode Forward Current vs. Voltage

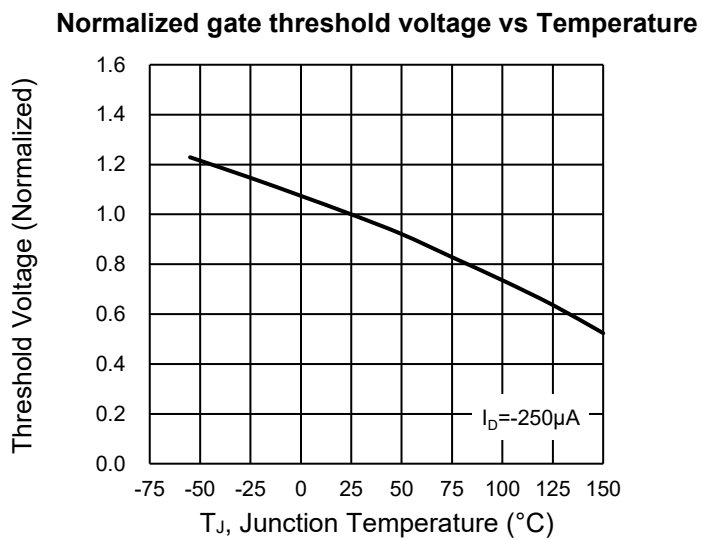
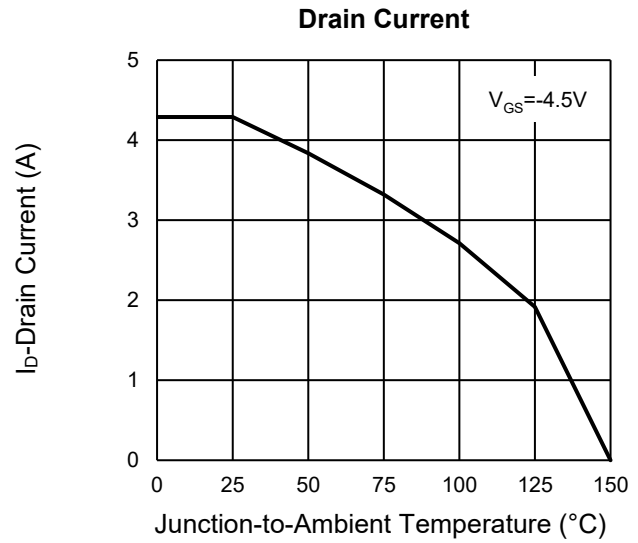
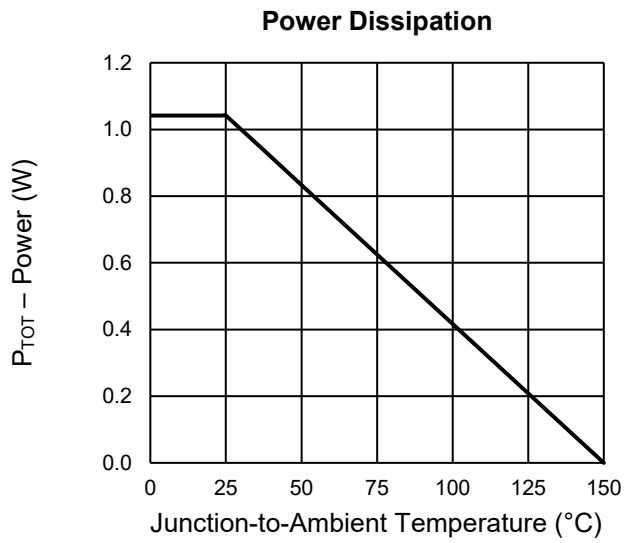


Normalized Thermal Transient Impedance, Junction-to-Ambient



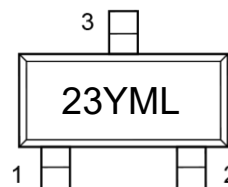
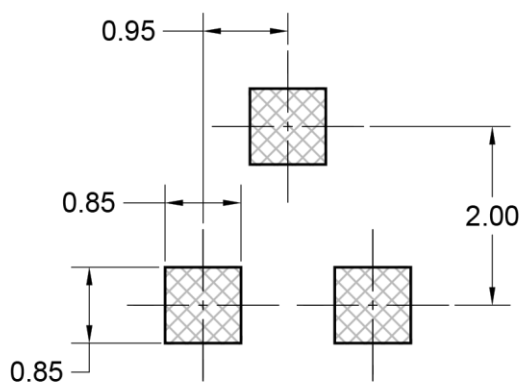
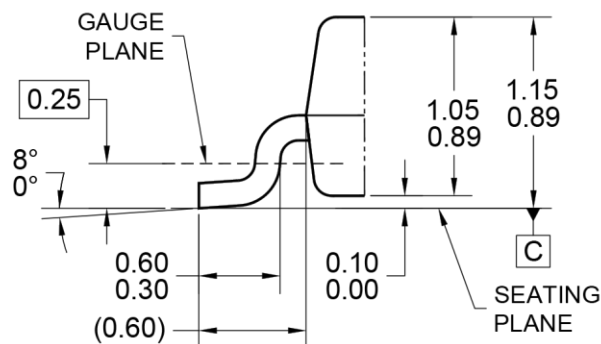
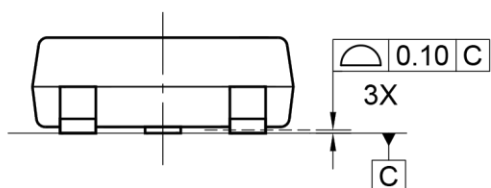
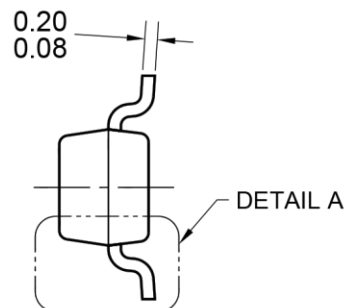
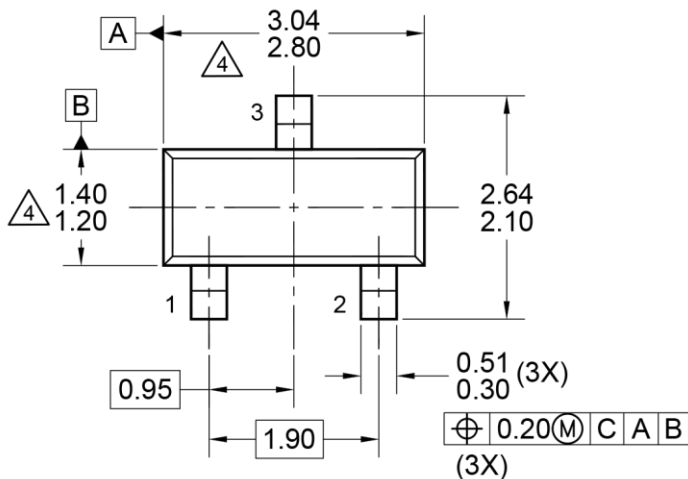
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

SOT-23



NOTES: UNLESS OTHERWISE SPECIFIED

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
3. PACKAGE OUTLINE REFERENCE: JEDEC TO-236, ISSUE H, VARIATION AA.
4. MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DWG NO. REF: HQ2SD07-SOT23JEDEC-104 REV A.

- MARKING DIAGRAM**
- 23 = Device marking
Y = Year Code
M = Month Code for Halogen Free Product
(O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
L = Lot Code

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